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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Tran, Mai-Huong

Sheet 1 of 2

Attorney Docket No: 303.716US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
	US-4,161,038	07/10/1979	Wu, S.	365	145	09/20/1977
	US-5,403,788	04/04/1995	Nishida, M. , et al.	501	32	04/21/1994
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	US-5,579,258	11/26/1996	Adachi, H.	365	145	11/27/1992
	US-5,635,433	06/03/1997	Sengupta, L.	501	137	09/11/1995
	US-5,744,374	04/28/1998	Moon, Jong	437	60	11/18/1996
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		CHO, I. H., "Highly Reliable Dual Gate Oxide Fabrication by Reducing Wet Etching Time and Re-Oxidation for Sub-Quarter Micron CMOS Devices", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999),pgs. 174-175	
		ETZOLD, K. F., "Ferroelectric and Piezoelectric Materials", <u>The Electrical Engineering Handbook</u> (computer file) : CRCnetBASE, (1999),pp. 1-13	
		GUO, X. , "High Quality Ultra-thin TiO2/Si3N4 Gate Dielectric for Giga Scale MOS Technology", <u>Technical Digest of 1998 IEDM</u> , (1998),pp. 377-380	
		HAN, B. M., "Chopping effect on the crystallinity of ZnO films prepared by a r.f. planar magnetron sputtering method", <u>Thin Solid Films</u> , 338, (1999),pp. 265-268	
		ISHIWARA, H. , "Proposal of a Novel Ferroelectric-Gate Field Effect Transistor with Seperated Functions for Data read-Out Data Storage", <u>Precision and Intelligence Laboratory, Tokyo Institute of Technology</u> ,pp. 222-223	
		KOBAYASHI, K. , "Mechanism of Photoinduced Charge Transfer in Co(Li)-Doped ZnO Film", <u>Japanese Journal of Applied Physics</u> , 31, (1992),pp. L 1079 - L 1082	
		MATSUO, KOUJI , et al., "Low Leakage TiO2 Gate Insulator formed by Ultrathin TiN Deposition and Low-Temperature Oxidation", <u>Japanese Journal of Applied Physics</u> , vol. 39, no. 10, (October 2000),5794-5799	
		NISHINO, J. , "Preparation of Zinc Oxide Films by Low-Pressure Chemical	

EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>	Complete if Known <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 40%;">Application Number</td> <td>Unknown</td> </tr> <tr> <td>Filing Date</td> <td>Even Date Herewith</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>Unknown</td> </tr> <tr> <td>Examiner Name</td> <td>Tran, Mai-Huong</td> </tr> </table>	Application Number	Unknown	Filing Date	Even Date Herewith	First Named Inventor	Ahn, Kie	Group Art Unit	Unknown	Examiner Name	Tran, Mai-Huong
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Filing Date	Even Date Herewith										
First Named Inventor	Ahn, Kie										
Group Art Unit	Unknown										
Examiner Name	Tran, Mai-Huong										
Sheet 2 of 2	Attorney Docket No: 303.716US2										

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Vapor Deposition Method", <u>Mat. Res. Soc. Symp. Proc.</u> , 363, (1995),pp. 219-224	
		ONODERA, A. , "Dielectric Activity and Ferroelectricity in Piezoelectric Semiconductor Li-Doped ZnO", <u>Jpn. J. Appl. Phys.</u> , 35, (1996),pp. 5160-5162	
		ONODERA, A. , "Ferroelectric Properties in Piezoelectric Semiconductor Zn1- M O (M=Li, Mg)", <u>Jpn. J. Appl. Phys.</u> , 36, (1997),pp. 6008-6011	
		SAITO, Y. , "High-Integrity Silicon Oxide Grown at Low-temperature by Atomic Oxygen Generated in High-Density Krypton Plasma", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , (1999),pp. 152-153	
		SUNTOLA, T. , "Atomic layer epitaxy", <u>Thin Solid Films</u> , 216, (1992),pp. 84-89	
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EXAMINER

DATE CONSIDERED

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Kie Y. Ahn et al.	Examiner:	Unknown
Serial No.:	Unknown	Group Art Unit:	Unknown
Filed:	Herewith	Docket:	303.716US2
Title:	STRUCTURES, METHODS, AND SYSTEMS FOR FERROELECTRIC MEMORY TRANSISTORS		

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Assistant Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. § 1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicants' prior U.S. application, Serial No. 09/809560, filed on March 15, 2001, which is relied upon for an earlier filing date under 35 U.S.C. § 120.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.


Respectfully submitted,

KIE Y. AHN ET AL.

By their Representatives,

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Date 20 June 2003

By 
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"Express Mail" mailing label number: EV332569295US

Date of Deposit: June 20, 2003

This paper or fee is being deposited on the date indicated above with the United States Postal Service pursuant to 37 CFR 1.10, and is addressed to The Commissioner for Patents, Mail Stop Patent Application, P.O.Box 1450, Alexandria, VA 22313-1450.